



Development of detailed ROOT geometry for the inner tracker detectors in the BM@N experiment

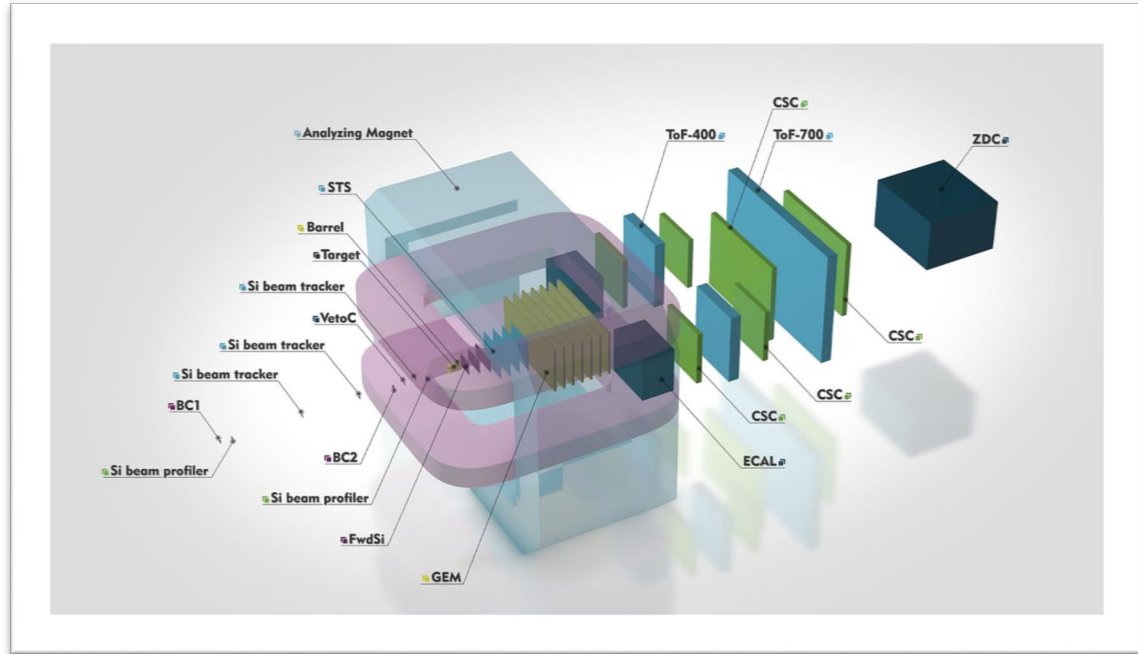
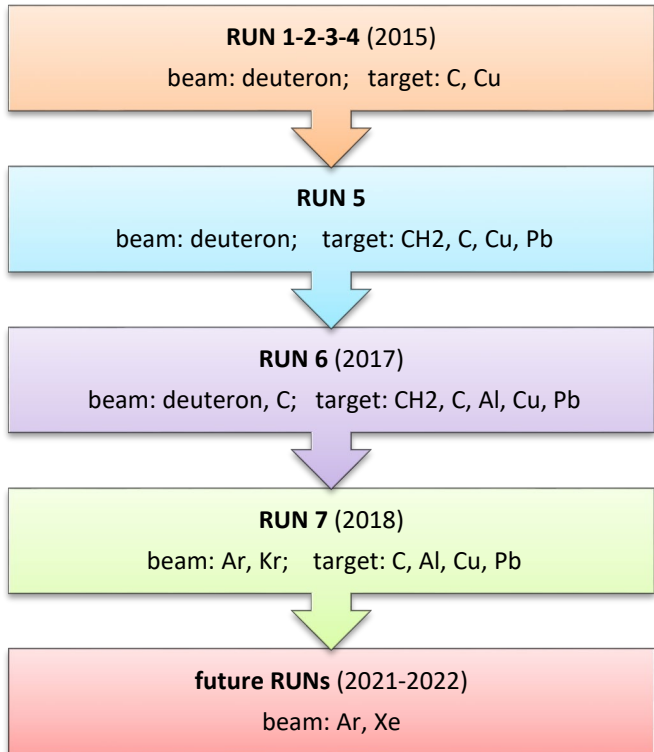
Baranov Dmitry

BM@N experiment

BM@N (Baryonic Matter at Nuclotron) is the first stage experiment at the accelerator complex of NICA.

It is a **fixed target experiment** aimed to study nuclear matter in the relativistic heavy ion collisions.

Since 2015 **seven BM@N RUNs** have been carried out:

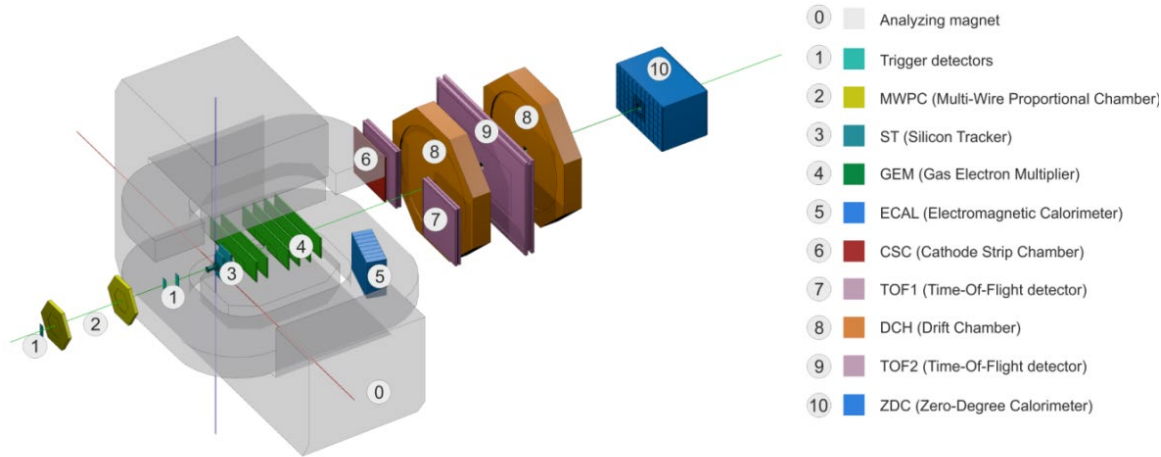


The full configuration of the BM@N setup for the next RUNs

The latest RUN was divided into two parts:

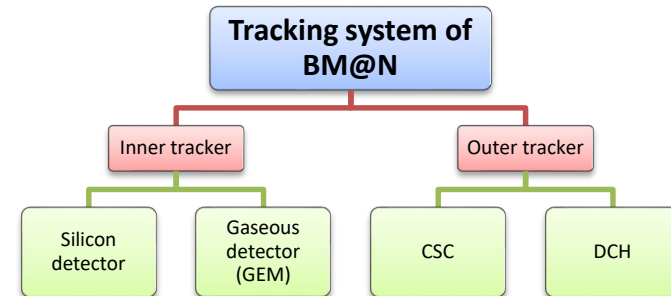
- Basic program of BM@N
- Additional program - SRC (Short Range Correlations)

Tracking system in BM@N



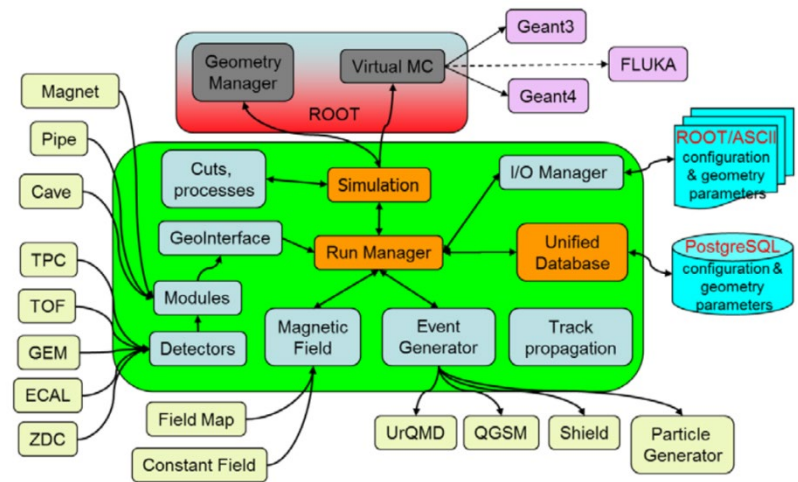
BM@N setup for the RUN-7 configuration

The complete tracking system of the BM@N setup is divided into the **inner** and **outer** trackers



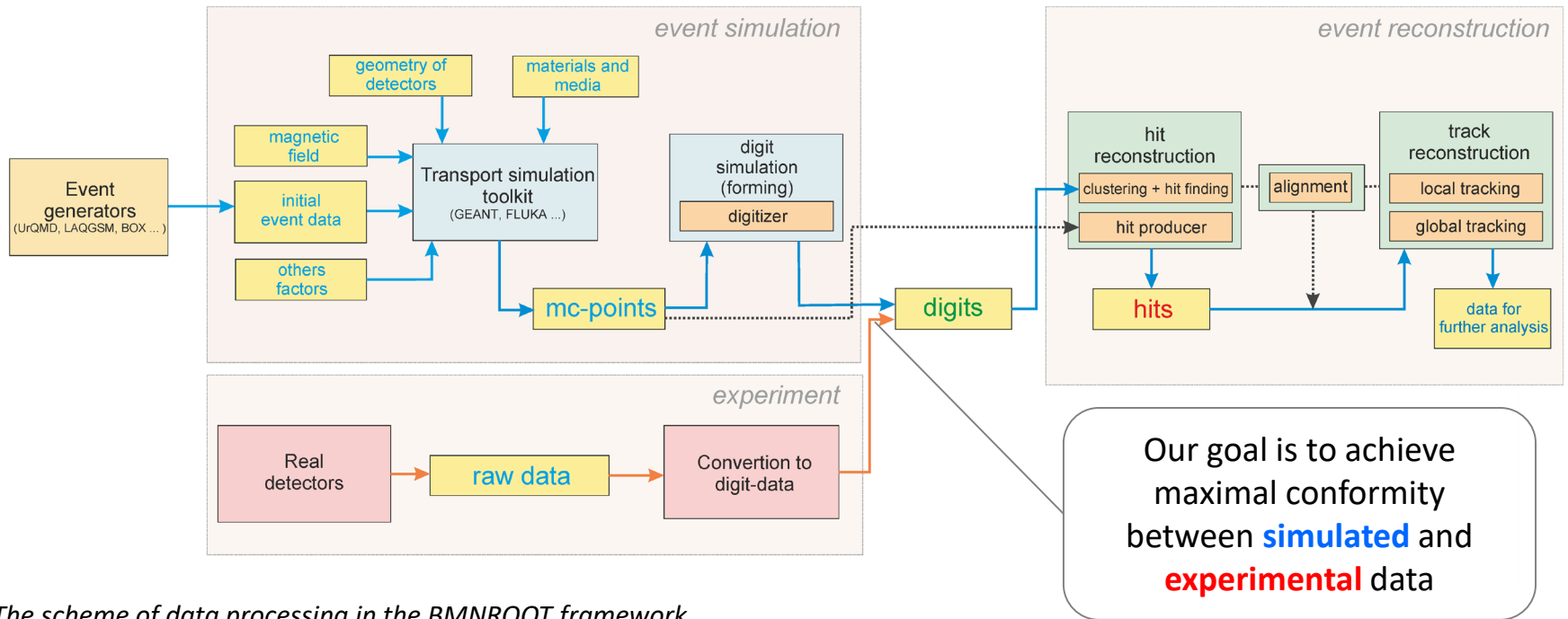
Framework **BMNROOT** was developed to support BM@N experiment.

It provides powerful tools for **simulations**, **reconstruction** and **data analysis**.

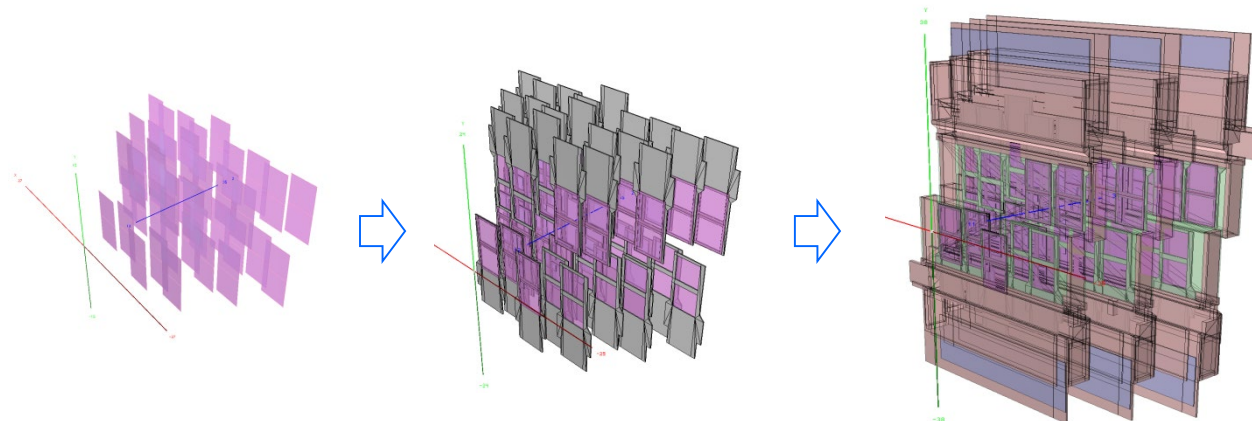


The scheme of the BMNROOT modules in the simulation

Why we need to use detailed ROOT geometry



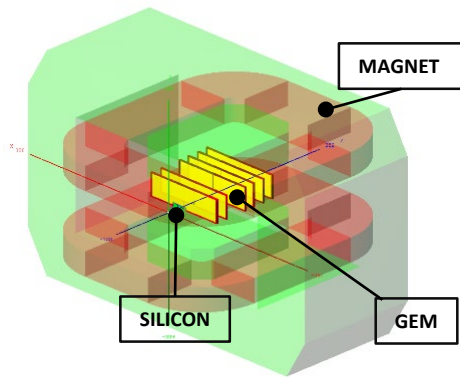
The scheme of data processing in the BMNROOT framework



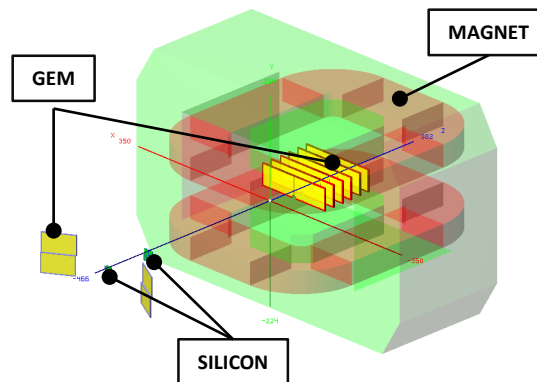
Refinement of the geometric model for the Forward Silicon detector

Detailed ROOT geometry: configurations

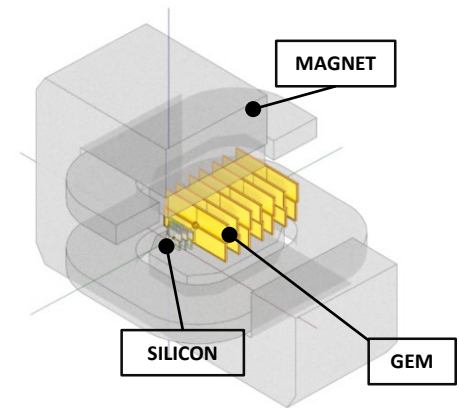
- ❑ The detailed ROOT geometry was created for the following configurations:
 - **GEM RUN-7** (spring, 2018)
 - **GEM RUN SRC** (spring, 2018)
 - **GEM Future Configuration** (2021-2022)
 - **Forward SILICON Future Configuration** (2021-2022)
- ❑ The design of these detector has a lot of supporting elements, such as frames, electronics and others. It influences the detector efficiency.
- ❑ There are two versions of the ROOT geometry (simplified and detailed) for each configuration.



SILICON and GEM detectors (RUN-7)

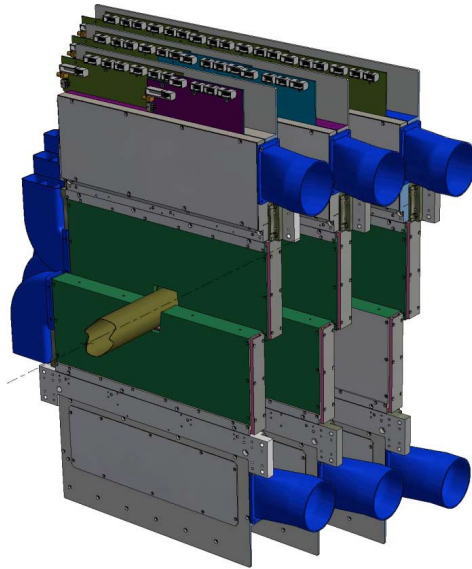


SILICON and GEM detectors (SRC)

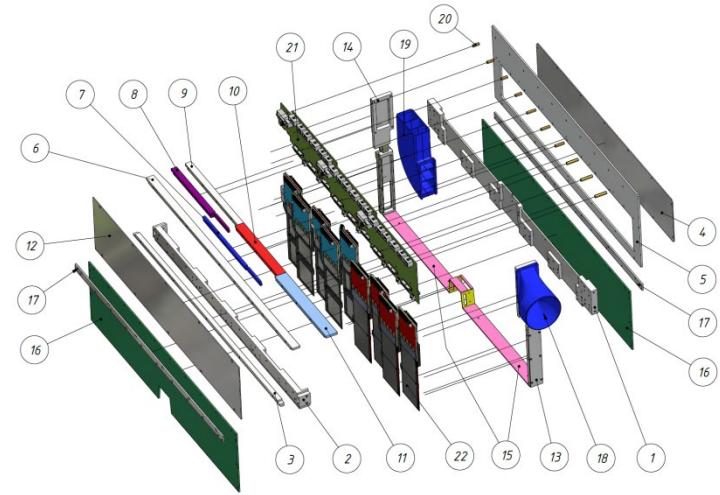


SILICON and GEM detectors (Future RUN)

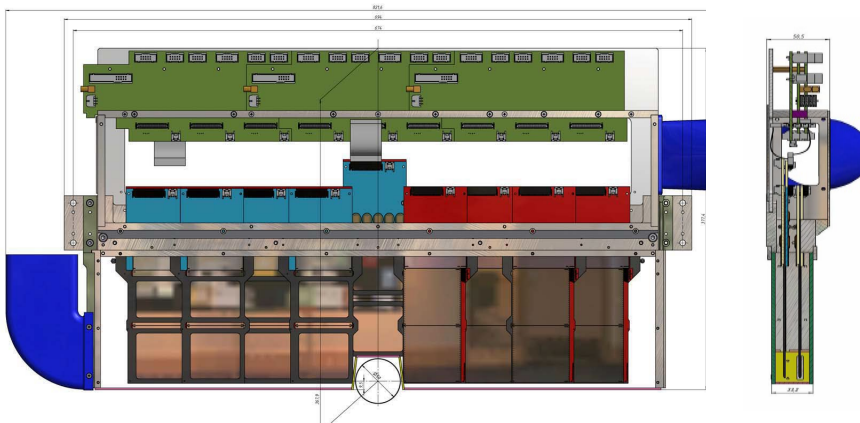
Forward Silicon detector



Full assembly of Forward Silicon detector



Parts of one half-plane of Forward Silicon Detector

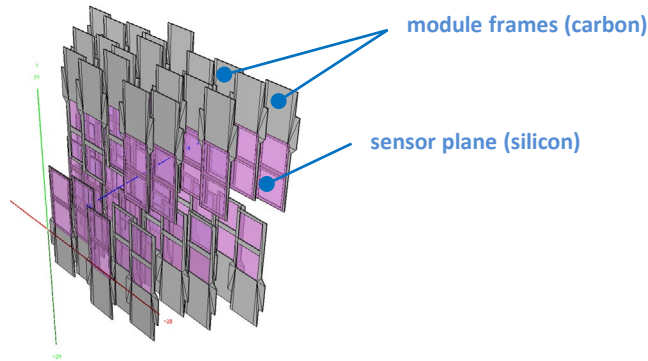
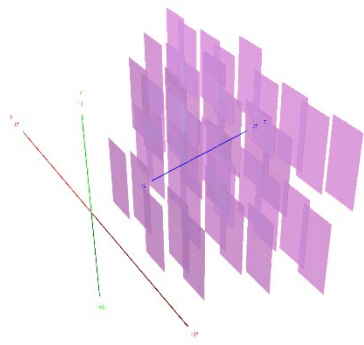


Scheme of one half-plane: front and side views

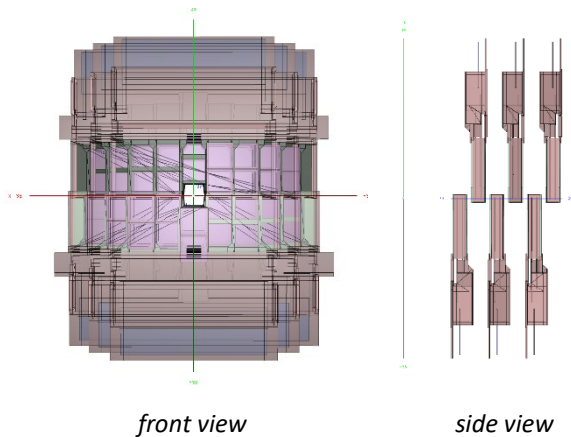
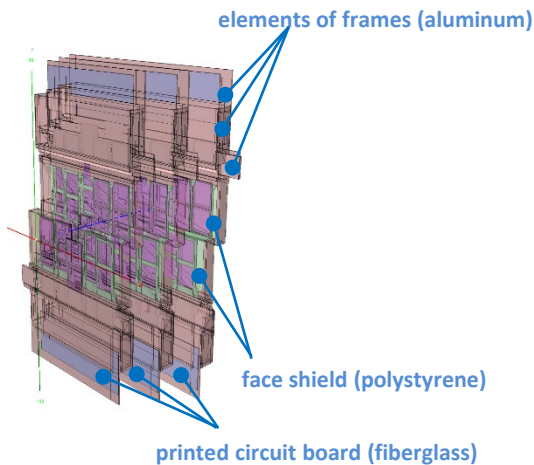
	Описание	Материал	Размер вдоль пучка	
1	Базовая планка	Алюминиевый сплав	8...14 мм	Вне чувствительной зоны Si-сensors
2	Планка	Алюминиевый сплав	6...12 мм	Вне чувствительной зоны Si-сensors
3	Планка	Алюминиевый сплав	10 мм	Вне чувствительной зоны Si-сensors
4	Пластина	Алюминиевый сплав	1.5 мм	Вне чувствительной зоны Si-сensors
5	Пластина	Алюминиевый сплав	3 мм	Вне чувствительной зоны Si-сensors
6...11	Рейки	Алюминиевый сплав	Суммарная толщина	Вне чувствительной зоны Si-сensors
12	Пластина	Алюминиевый сплав	1.5 мм	Вне чувствительной зоны Si-сensors
13	Боковая стенка экрана	Алюминиевый сплав	27 мм	Вне чувствительной зоны Si-сensors
14	Боковая стенка экрана	Алюминиевый сплав	27 мм	Вне чувствительной зоны Si-сensors
15	Горизонтальная стенка экрана	Пенопласт	27 мм	В чувствительной зоне Si-сensors
16	Лицевая стенка экрана	Пенопласт	3 мм	В чувствительной зоне Si-сensors
17	Планка экрана	Алюминиевый сплав	3 мм	Вне чувствительной зоны Si-сensors
18...19	Тонкостенный патрубок	Пластик АБС	Стенка - 2 мм	Вне чувствительной зоны Si-сensors
20	Втулки крепления плат электроники	Латунь	25 мм	Вне чувствительной зоны Si-сensors
21	Платы электроники	Стеклотекстолит	2 мм + компоненты	Вне чувствительной зоны Si-сensors
22	Модули Si-сensors и электроники			

Description of the parts

Forward Silicon detector: ROOT geometry



Simplified ROOT geometry: only sensitive planes (left) and sensitive planes with carbon frames (right)



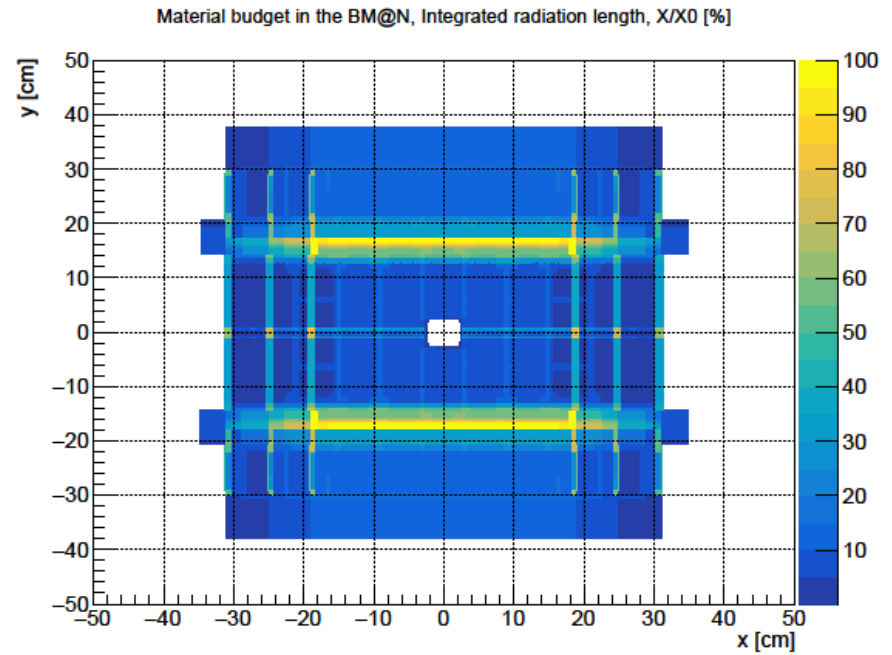
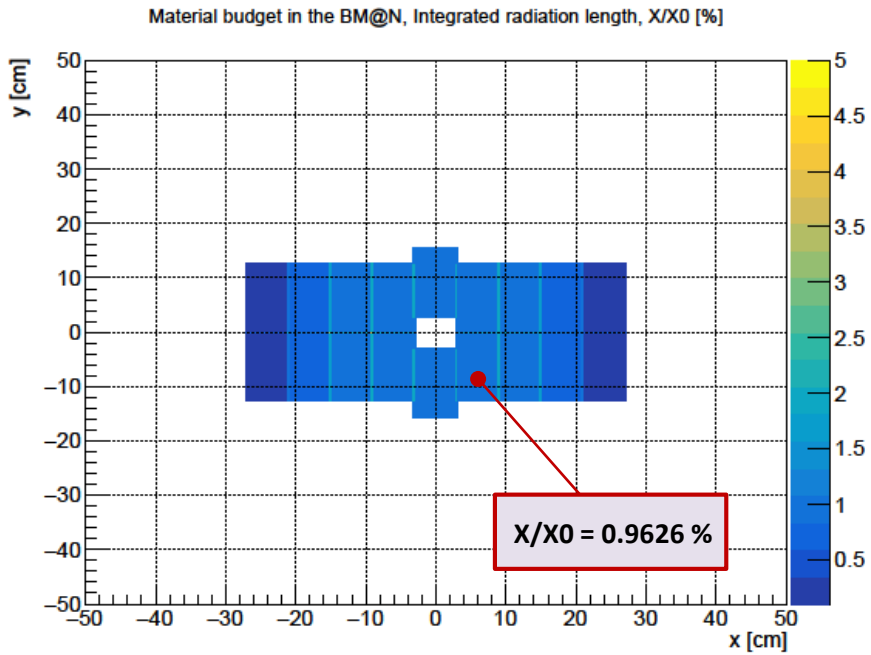
Detailed ROOT geometry: sensitive planes and supporting elements (passive volumes)

passive elements in each SI-station

- module-frame2_station0_0
- module3_station0_0
- moduleFrame3_station0_0
- module4_station0_0
- moduleFrame4_station0_0
- module5_station0_0
- moduleFrame5_station0_0
- module6_station0_0
- moduleFrame6_station0_0
- module7_station0_0
- moduleFrame7_station0_0
- module8_station0_0
- moduleFrame8_station0_0
- module9_station0_0
- moduleFrame9_station0_0
- frames_station0_0
- faceShieldV_station0_0
- faceShieldV_station0_1
- faceShieldV_station0_2
- faceShieldV_station0_3
- sideShieldV_station0_0
- sideShieldV_station0_1
- sideShieldV_station0_2
- sideShieldV_station0_3
- horizShieldV_station0_0
- horizShieldV_station0_1
- horizShieldV_station0_2
- horizShieldV_station0_3
- plankShieldV_station0_0
- plankShieldV_station0_1
- plankShieldV_station0_2
- plankShieldV_station0_3
- baseRailV_station0_0
- baseRailV_station0_1
- backRailV_station0_0
- backRailV_station0_1
- holdBackRailV_station0_0
- holdBackRailV_station0_1
- backPlaneV_station0_0
- backPlaneV_station0_1
- frontPlaneV_station0_0
- frontPlaneV_station0_1
- frontPlaneWithWindowV_station0_0
- frontPlaneWithWindowV_station0_1
- pcbV_station0_0
- pcbV_station0_1
- upperSideShieldV_station0_0
- upperSideShieldV_station0_1
- upperSideShieldV_station0_2
- upperSideShieldV_station0_3
- upperSideShieldCoverV_station0_0
- upperSideShieldCoverV_station0_1
- upperSideShieldCoverV_station0_2
- upperSideShieldCoverV_station0_3
- station1_0
- station2_0

Hierarchical structure of ROOT geometry

Forward Silicon detector: material budget

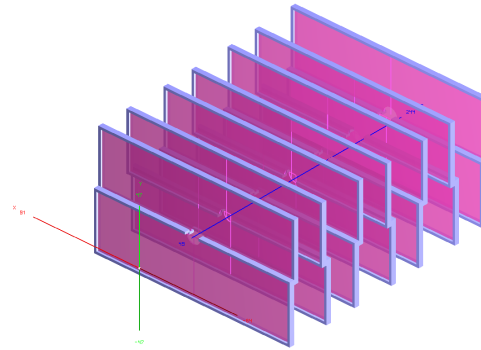


Material budget for the Forward Silicon Detector:
Left – simplified geometry (only sensitive planes), right – detailed geometry

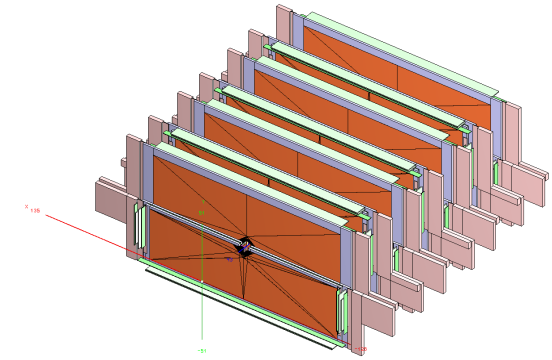
GEM: configuration for the next RUN (2021-2022)

The **configuration for the next RUN** consists of seven GEM stations located inside the magnet along the beam axis (axis Z).

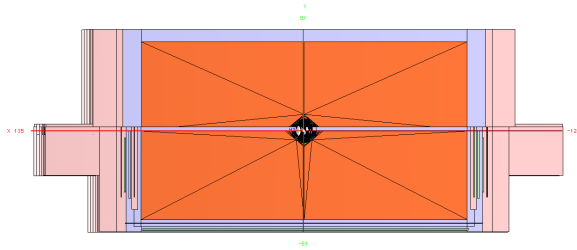
One station in this configuration is represented by two GEM half-planes – upper and lower, with the sizes of 163x45 cm for each.



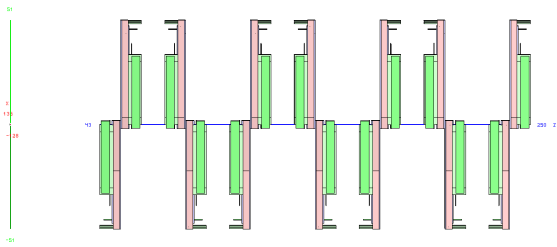
Simplified ROOT geometry of GEMs for the next run: only sensitive planes and ordinary frames.



Detailed ROOT geometry of GEMs for the next run: passive elements (such as frames, electronics and material layers in sensitive areas) were added.



Detailed geometry of GEMs for the next run: front view (XY)



Detailed geometry of GEMs for the next run: side view (ZY)

Верхняя пл		
ПОЗ	НОМЕР ДЕТАЛИ	КОЛ
1	Верхние блоки эпоксид	1
2	чувствительная обл	1
3	нижние блоки эпоксид	1
4	Al кронштейн пр	1
5	Блок усилителей внешн пр	1
6	Блок усилителей внутр пр	1
7	печатная плата внешн пр	1
8	Al поддержка кабелей пр	1
9	печатная плата внутр пр	1
10	Al поддержка кабелей лев	1
11	печатная плата внутр лев	1
12	печатная плата внешн лев	1
13	Блок усилителей внутр лев	1
14	Блок усилителей внешн лев	1
15	Al кронштейн лев	1
16	Блок печатных плат задн	1
17	Блок усилителей внутр задн	1
18	Блок усилителей внешн задн	1
19	эл-т верт. пласк. пр	1
20	эл-т верт. пласк. лев	1
21	эл-т верт. пласк. внешн лев	1
22	эл-т верт. пласк. внешн пр	1

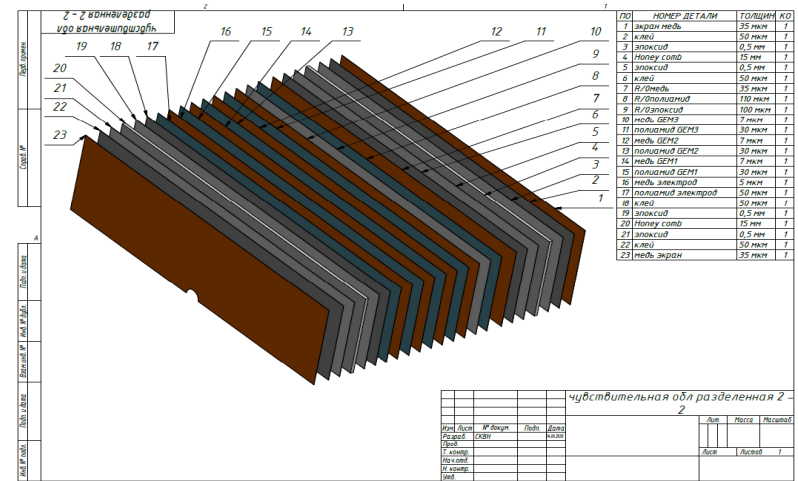
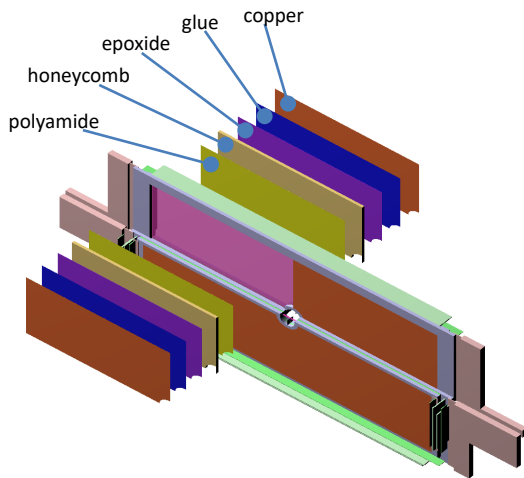
Нижняя пл		
ПОЗ	НОМЕР ДЕТАЛИ	КОЛ
1	Верхние блоки эпоксид	1
2	чувствительная обл	1
3	нижние блоки эпоксид	1
4	Al кронштейн пр	1
5	Блок усилителей внешн пр	1
6	Блок усилителей внутр пр	1
7	печатная плата внешн пр	1
8	Al поддержка кабелей пр	1
9	печатная плата внутр пр	1
10	Al поддержка кабелей лев	1
11	печатная плата внутр лев	1
12	печатная плата внешн лев	1
13	Блок усилителей внутр лев	1
14	Блок усилителей внешн лев	1
15	Al кронштейн лев	1
16	Блок печатных плат задн	1
17	Блок усилителей внутр задн	1
18	Блок усилителей внешн задн	1
19	эл-т верт. пласк. пр	1
20	эл-т верт. пласк. лев	1
21	эл-т верт. пласк. внешн лев	1
22	эл-т верт. пласк. внешн пр	1

Drawing of two GEM half-planes (upper and lower) for the future runs

GEM: sensitive area structure

Besides frames and electronic elements, layers of materials in sensitive areas have been added to the detailed geometry.

The thickness of some layer is a summarized thickness of all layers with the same material.



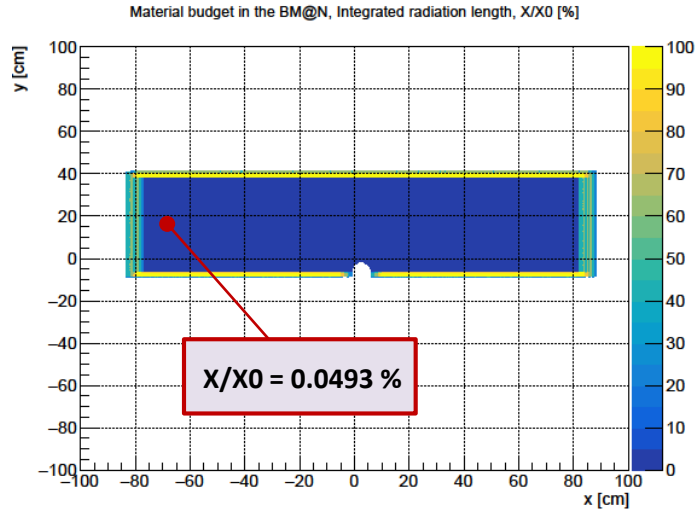
Layer structure of a sensitive area for one half-plane of GEM (prepared by the GEM group)

- copper:** 35μm + 35μm + 7μm + 7μm + 7μm + 5μm + 35μm = **131μm**
- glue:** 50μm + 50μm + 50μm + 50μm = **200μm**
- epoxide:** 0.5mm + 0.5mm + 100μm + 0.5mm + 0.5mm = **2.1mm**
- honeycomb:** 15mm + 15mm = **30mm**
- polyamide:** 110μm + 30μm + 30μm + 30μm + 50μm = **250μm**

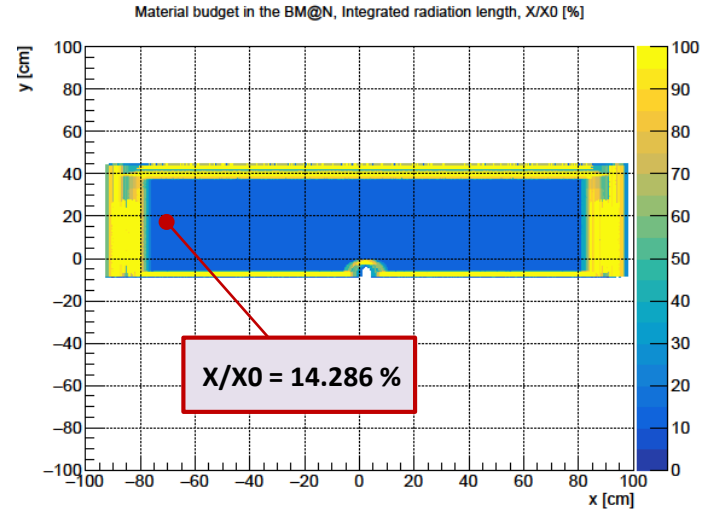
layer	material	density [g/cm-3]	thickness (X) [cm]	X0 [cm]	X/X0 [%]
gas	ArCO2 (70/30)	0.0019	0.9	10960.2	0.0082
copper	copper	8.96	0.0131	1.435	0.9129
glue	acrylic glue	1.25	0.02	32.1603	0.0622
	polyurethane (high dens.)	1.8	0.21	22.5351	0.9319
	polyurethane (medium dens.)	0.59	0.21	68.7512	0.3055
epoxide	polyurethane (low dens.)	0.25	0.21	162.253	0.1295
	nomex aramid honeycomb (kevlar chemical structure)	0.048	3.0	755.397	0.3971
honeycomb	polyamide	1.14	0.025	36.4052	0.0687

Table: properties of material layers in the sensitive area of GEM chambers

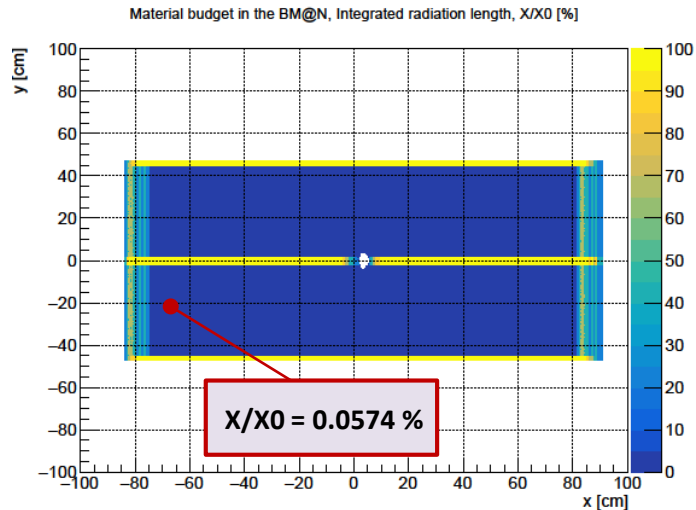
GEM: material budget



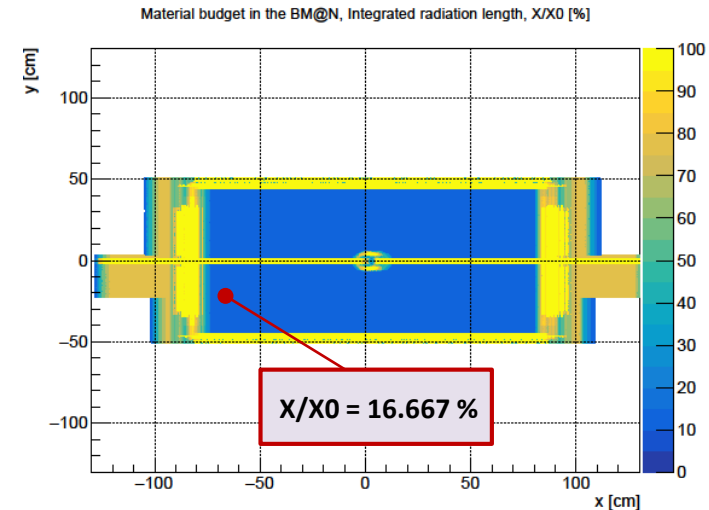
Material budget of six stations for tracks parallel to Z axis (simplified geometry)



Material budget of six stations for tracks parallel to Z axis (detailed geometry)



Material budget of seven stations for tracks parallel to Z axis (simplified geometry)



Material budget of seven stations for tracks parallel to Z axis (detailed geometry)

Summary

- ✓ The detailed geometry for the inner tracker detectors (GEM and SILICON) of the BM@N setup was prepared for the following runs:
 - RUN-7 (2018)
 - the next run (2021-2022)
- ✓ The material budget distribution for each configuration was calculated

Thank you for your attention...